

**IN THE SPECIFICATION**

Please amend the Specification as follows:

Page 1, line 6, please amend the paragraph starting there-at as follows:

"This application is a continuation-in-part of U.S. Patent Application No. 09/712,449 entitled "VERTICAL JUNCTION FIELD EFFECT SEMICONDUCTOR DIODES" filed by Richard A. Metzler on November 13, 2000, now issued as U.S. Pat. No. 6,580,150 B1."

Page 1, line 10, please amend the paragraph starting there-at as follows:

"Furthermore, this application is related to U.S. Patent Application No. 09/689,074 entitled "METHOD AND APPARATUS FOR PATTERNING FINE DIMENSIONS" filed by Richard A. Metzler on October 12, 2000, now issued as U.S. Pat. No. 6,667,237 B1, and U.S. Patent Application No. 09/502,026 entitled "METHOD AND APPARATUS FOR CYLINDRICAL SEMICONDUCTOR DIODES" filed by Richard A. Metzler on February 10, 2000, now issued as U.S. Pat. No. 6,433,370 B1."

Page 28, line 18, please amend the three consecutive paragraphs starting there-at and continuing to page 29, line 16 as follows:

"Referring now to Figures 11A and 11B, a substrate 1301 is covered with a uniform layer 1302 of material1 and a uniform layer 1303 of material2. A thick layer

[[200]] of material2 is then deposited on top of the uniform layer [[303]] 1303. The thick layer [[200]] of material2 is then patterned using a mask to form pedestals [[200']] 1200'. The mask has repetitive patterns of oval geometric shapes to form the oval construction pedestals [[200']] 1200' illustrated in Figures 11A and 11B.

Referring now to Figure 12A and 12B, sidewalls [[210']] 1210' of material1 are formed around the construction pedestals [[200']] 1200'. Between the repetitive pattern of sidewalls [[210']] 1210' is a space [[209']] 1209'. The top view as illustrated by Figure 12A, shows the oval cylinders of the sidewalls [[210']] 1210' concentric with the construction pedestals [[200']] 1200'.

Referring now to Figures 13A and 13B, the pedestals [[200']] 1200' of material2 and exposed portions of the uniform layer [[303]] 1303 are removed by an etching step leaving a repetitive pattern of hollow cylindrical sidewalls [[210']] 1210' having a cross-section of the width of the sidewall. Spaces [[214]] 1214 are formed therein, while spaces [[209']] 1209' remain between adjacent sidewalls [[210']] 1210'. A hollow cylindrical portion [[303']] 1303' of the uniform layer [[303]] 1303 remains intact under the hollow cylindrical sidewalls [[210']] 1210'. The uniform layer [[302]] 1302 may provide an etch stop to keep unexposed portions of the substrate [[301]] 1301 from being etched. However, if the pattern of sidewalls [[210']] 1210' has the desired pitch, further division of the initial pitch is not needed and the process can jump to processing the substrate [[301]] 1301 and the uniform layer [[302]] 1302."